

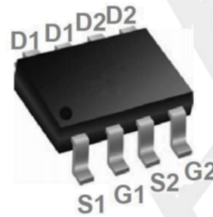
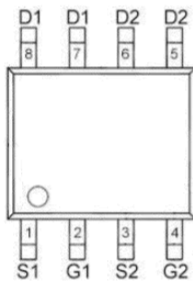
Application

- Reverse Battery protection
- Load switch
- Power management
- Motor Control
- Portable Power Adaptors

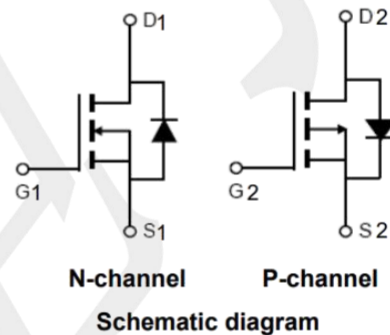
Product Summary

Device	BV _{DSS}	R _{DS(ON)MAX}	I _D MAX TA=25°C
Q1 N-Channel	40V	26mΩ@ VGS=10V	7.2A
		35mΩ@VGS=4.5V	5.2A
Q2 P-Channel	-40V	38mΩ@VGS=10V	-7.5A
		58mΩ@VGS=4.5V	-5.5A

Package and Pin Configuration



Circuit diagram



Marking:4614B

Absolute Maximum Ratings

(@ TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Q1	Q2	Unit	
		N-CHANNEL	P-CHANNEL		
Drain-Source Voltage	V _{DSS}	40	-40	V	
Gate-Source Voltage	V _{GSS}	±20	±20	V	
Continuous Drain Current N-Channel: VGS = 10V P-Channel: VGS = -10V	Steady State	TA=25°C	7.2	-7.5	A
		TA=70°C	6.2	-6.5	A
Maximum Continuous Body Diode Forward Current (Note 1)	I _S	5	-5.5	A	
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I _{DM}	30	-32	A	

Notes: 1. Device mounted on 1" × 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

Thermal Characteristic

PARAMETER	Symbol	Value	Unit
Total Power Dissipation (Note 1)	PD	2	W
Thermal Resistance, Junction to Ambient (Note 1)	R _{θJA}	62.5	°C/W
Thermal Resistance, Junction to Case (Note 1)	R _{θJC}	15	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics Q1 N-CHANNEL

(@ TA = +25°C, unless otherwise specified.)

PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS (Note 2)							
Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	BVDSS	40	--	--	V	
Zero Gate Voltage Drain Current T _J = +25°C	V _{DS} =20V, V _{GS} = 0V	I _{DSS}	--	--	1	μA	
Gate-Source Leakage	V _{DS} =0V, V _{GS} = ±8V	I _{GSS}	--	--	±100	nA	
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	V _{GS(TH)}	0.65	--	2.5	V	
Static Drain-Source On-Resistance	V _{GS} =10V, I _D =7.2A	R _{DS(on)}	--	24	26	mΩ	
	V _{GS} =4.5V, I _D =5A		--	32	35		
Diode Forward Voltage	V _{GS} = 0V, I _S = 5A	V _{SD}	--	0.7	1.2	V	
DYNAMIC CHARACTERISTICS (Note 3)							
Input Capacitance	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz	C _{iss}	--	700	--	pF	
Output Capacitance		C _{oss}	--	92	--		
Reverse Transfer Capacitance		C _{rss}	--	80	--		
Total Gate Charge (V _{GS} = 4.5V)	V _{DS} = 10V, I _D =5A	Q _g	--	9.4	--	nC	
Total Gate Charge (V _{GS} = 10V)			--	18	--		
Gate-Source Charge			Q _{gs}	--	0.6		--
Gate-Drain Charge			Q _{gd}	--	2		--
Turn-On Delay Time	V _{DD} = 10V, V _{GS} = 4.5V, I _D =1A, R _G = 1Ω	t _{D(ON)}	--	5	--	nS	
Turn-On Delay Time		t _R	--	14.4	--		
Turn-Off Delay Time		t _{D(OFF)}	--	30	--		
Turn-Off Fall Time		t _F	--	9.2	--		
Body Diode Reverse Recovery Time	I _S = 5A, dI/dt = 100A/μs	t _{RR}	--	7.6	--		
Body Diode Reverse Recovery Charge	I _S = 5A, dI/dt = 100A/μs	Q _{RR}	--	0.9	--	nC	

- Notes:**
2. Short duration pulse test used to minimize self-heating effect.
 3. Guaranteed by design. Not subject to product testing.

Electrical Characteristics Q2 P-CHANNEL

(@ TA = +25°C, unless otherwise specified.)

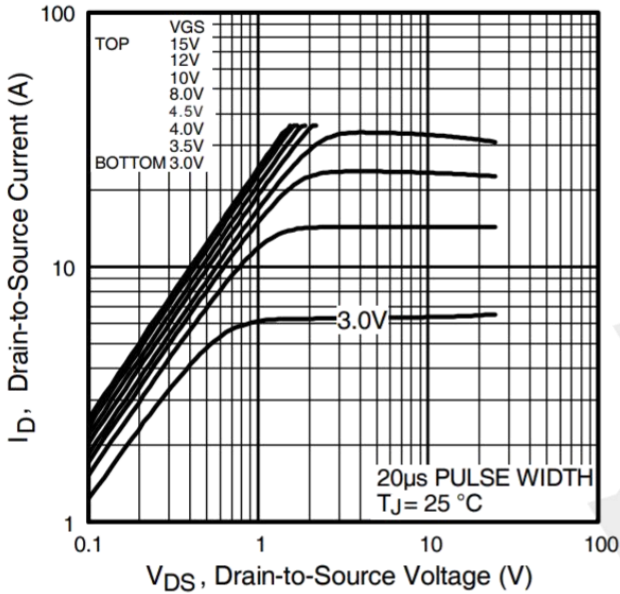
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS (Note 2)							
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	BVDSS	-40	--	--	V	
Zero Gate Voltage Drain Current $T_J = +25^\circ C$	$V_{DS}=-20V, V_{GS}= 0V$	I_{DSS}	--	--	-1	μA	
Gate-Source Leakage	$V_{DS}=0V, V_{GS}= \pm 8V$	I_{GSS}	--	--	± 100	nA	
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu A$	$V_{GS(TH)}$	-0.65	--	-2.5	V	
Static Drain-Source On-Resistance	$V_{GS}=-10V, I_D=-7.5A$	$R_{DS(on)}$	--	36	38	m Ω	
	$V_{GS}=-4.5V, I_D=-5A$		--	55	58		
Diode Forward Voltage	$V_{GS} = 0V, I_S = -5A$	VSD	--	-0.7	-1.2	V	
DYNAMIC CHARACTERISTICS (Note 3)							
Input Capacitance	$V_{DS} = -10V,$ $V_{GS} = 0V,$ $f = 1.0MHz$	C_{iss}	--	710	--	pF	
Output Capacitance		C_{oss}	--	94	--		
Reverse Transfer Capacitance		C_{rss}	--	85	--		
Total Gate Charge ($V_{GS} = -4.5V$)	$V_{DS} = -10V, I_D = -5A$	Q_g	--	9.6	--	nC	
Total Gate Charge ($V_{GS} = -10V$)			--	19	--		
Gate-Source Charge			Q_{gs}	--	0.8		--
Gate-Drain Charge			Q_{gd}	--	2.5		--
Turn-On Delay Time	$V_{DD} = -10V,$ $V_{GS} = -4.5V,$ $I_D = -1A, R_G = 1\Omega$	$t_{D(ON)}$	--	5.6	--	nS	
Turn-On Delay Time		t_R	--	14.8	--		
Turn-Off Delay Time		$t_{D(OFF)}$	--	35	--		
Turn-Off Fall Time		t_F	--	9.8	--		
Body Diode Reverse Recovery Time	$I_S = -5A, dI/dt = 100A/\mu s$	t_{RR}	--	7.9	--	nC	
Body Diode Reverse Recovery Charge	$I_S = -5A, dI/dt = 100A/\mu s$	Q_{RR}	--	1.1	--		

Notes: 2. Short duration pulse test used to minimize self-heating effect.

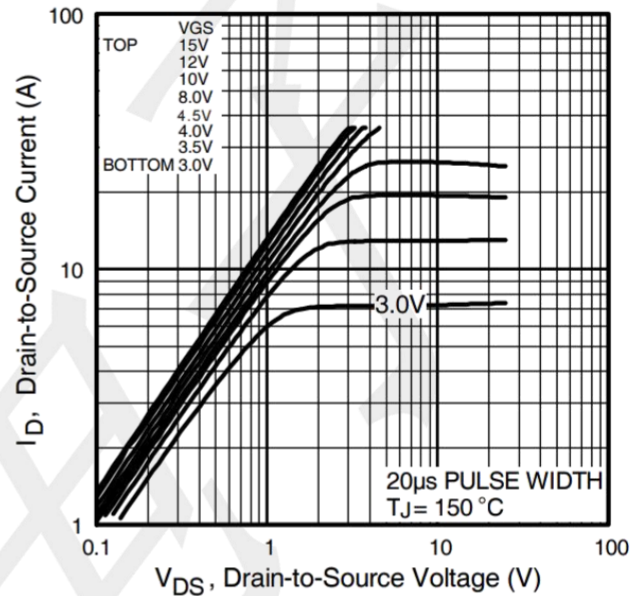
3. Guaranteed by design. Not subject to product testing.

Typical Performance Characteristics(TA=25°C unless otherwise Specified)

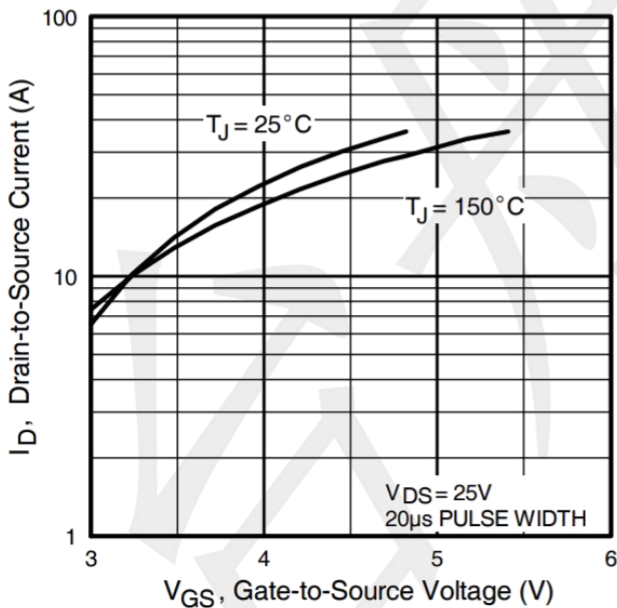
Q1 N-CHANNEL



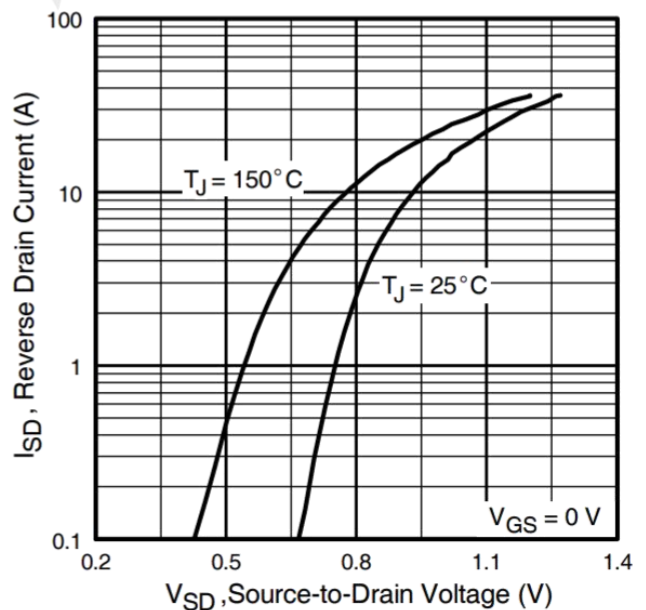
Typical Output Characteristics



Typical Output Characteristics

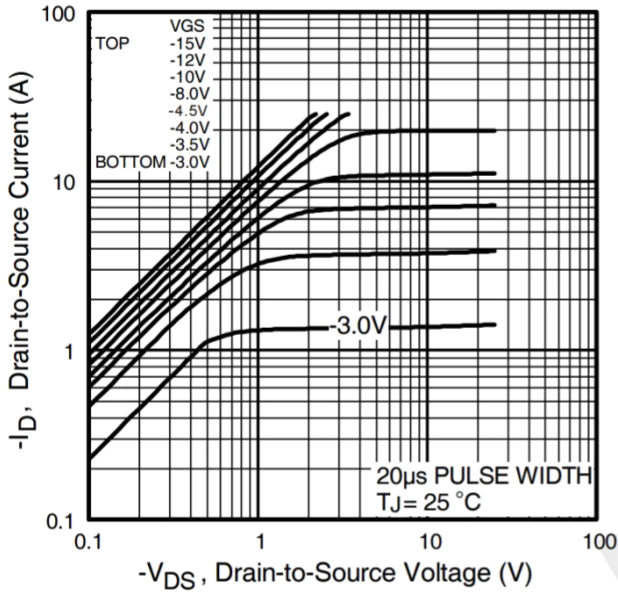


Typical Transfer Characteristics

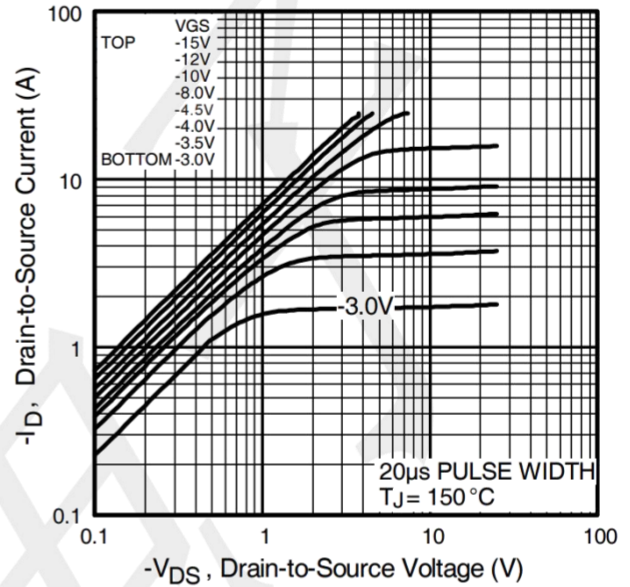


Typical Source-Drain Diode Forward Voltage

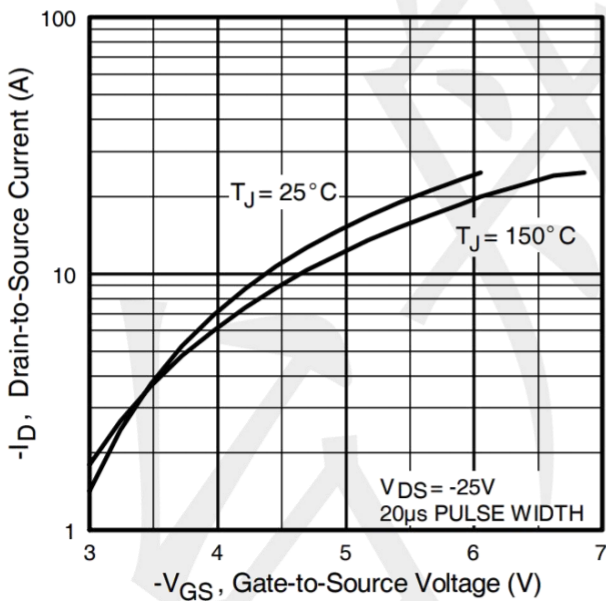
Typical Performance Characteristics(TA=25°C unless otherwise Specified)
Q2 P-CHANNEL



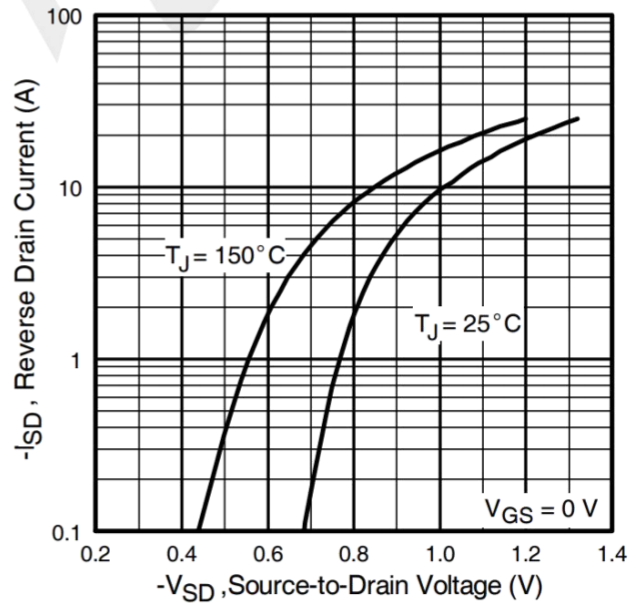
Typical Output Characteristics



Typical Output Characteristics



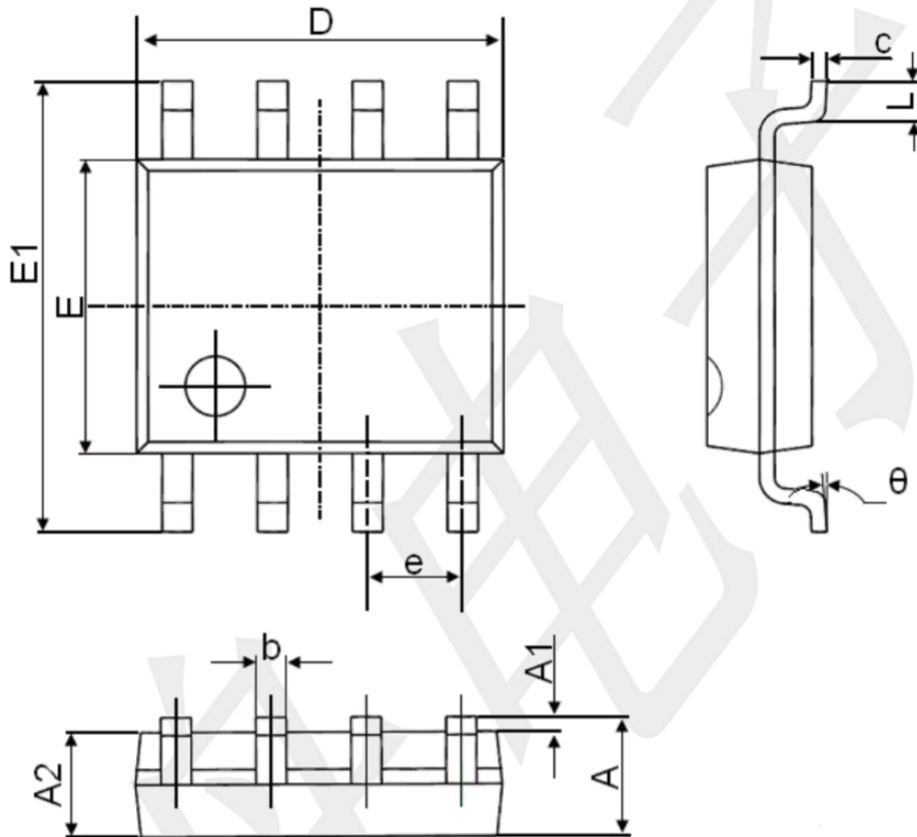
Typical Transfer Characteristics



Typical Source-Drain Diode Forward Voltage

Package Outline Dimensions (Unit: mm)

SOP8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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